

Page i

DIODES, MICROWAVE, SILICON, TUNING VARACTOR, BASED ON TYPES ML4355 THRU ML4365 ESCC Detail Specification No. 5512/007

ISSUE 1 October 2002





ESCC Detail Specification

PAGE	ii
ISSUE	1

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2002. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or allleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Ageny and provided that it is not used for a commercial purpose, may be:

- copied in whole in any medium without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



european space agency agence spatiale européenne

Pages 1 to 24

DIODES, MICROWAVE, SILICON, TUNING VARACTOR, BASED ON TYPES ML4355 THRU ML4365 ESA/SCC Detail Specification No. 5512/007



space components coordination group

Date		
	SCCG Chairman	ESA Director Genera or his Deputy
May 1993	Commens	Elik
May 2000	Sannot	Alons
-		May 1993 Francis



Rev. 'A'

PAGE 2

ISSUE 1

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
'A'	May '00	Table 5(b) Figure 5 en Figure 5 (b) P13. Para. 4.2.1 : Deviations Deviation (Para. 4.2.2 : Deviation (Para. 4.2.3 : Deviation (Para. 4.7.3 : New parage Existing amended P20. Table 5(a) : Title amen Table 5(b) : Title amen Existing Table 5(b) : Renumber Figure 5 : Renumber Figure 5(b) : New Figure P21. Para. 4.8.3 : In the second	ded ble deleted and new Table added ed as "5(a)"	None None 221551 221551 221551 221551 221551 221551 221551 221551 221551 221551 221551 221551 221551



PAGE 3

ISSUE 1

TABLE OF CONTENTS

1.	GENERAL	<u>Page</u> 5
1.1	Scope	5
1.2	Type Variants	5
1.3	Maximum Ratings	5
1.4	Parameter Derating Information	5
1.5	Physical Dimensions	5
1.6	Functional Diagram	5
1.7	Handling Precautions	5
2.	APPLICABLE DOCUMENTS	5
3.	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	5
4.	REQUIREMENTS	13
4.1	General	13
4.2	Deviations from Generic Specification	13
4.2.1	Deviations from Special In-process Controls	13
4.2.2	Deviations from Final Production Tests	13
4.2.3	Deviations from Burn-in and Electrical Measurements	13
4.2.4	Deviations from Qualification Tests	13
4.2.5	Deviations from Lot Acceptance Tests	13
4.3	Mechanical and Environmental Requirements	13
4.3.1	Dimension Check	13
4.3.2	Weight	14
4.3.3	Terminal Strength	14
4.4	Materials and Finishes	15
4.4.1 4.4.2	Case	15
4.4.2 4.5	Lead Materials and Finish	15
4.5 4.5.1	Marking General	15
4.5.1	Cathode Identification	15
4.5.2	The SCC Component Number	15
4.5.4	Traceability Information	15 16
4.6	Electrical Measurements	16
4.6.1	Electrical Measurements at Room Temperature	16
4.6.2	Electrical Measurements at High and Low Temperatures	16
4.6.3	Circuits for Electrical Measurements	16
4.7	Burn-in Tests	16
4.7.1	Parameter Drift Values	16
4.7.2	Conditions for High Temperature Reverse Bias Burn-in	16
4.7.3	Electrical Circuit for High Temperature Reverse Bias Burn-in	16
4.8	Environmental and Endurance Tests	21
4.8.1	Electrical Measurements on Completion of Environmental Tests	21
4.8.2	Electrical Measurements at Intermediate Points and on Completion of Endurance Tests	21
4.8.3	Conditions for Operating Life Tests	21
4.8.4	Electrical Circuits for Operating Life Tests	21
4.9	Total Dose Irradiation Testing	21
4.9.1	Application	21
4.9.2	Bias Conditions	21
4.9.3	Electrical Measurements	21
4.10	Special Testing	21



Rev. 'A'

PAGE 4 ISSUE 1

TABLE	<u>:s</u>	Page
1(a)	Type Variants	6
1(b)	Maximum Ratings	8
2	Electrical Measurements at Room Temperature - D.C. Parameters	17
	Electrical Measurements at Room Temperature - A.C. Parameters	17
3	Electrical Measurements at High and Low Temperatures	18
4	Parameter Drift Values	18
5(a)	Conditions for High Temperature Reverse Bias Burn-in and Operating Life Tests	20
5(b)	Conditions for Power Burn-in	20
6 7	Electrical Measurements at Intermediate Points and on Completion of Endurance Testing Electrical Measurements During and on Completion of Irradiation Testing	22 23
FIGUR		
1	Parameter Derating Information	0
2	Physical Dimensions	8 9
3	Functional Diagram	12
4	Circuits for Electrical Measurements	19
5(a)	Electrical Circuit for High Temperature Reverse Bias Burn-in and Operating Life Tests	20
5(b)	Electrical Circuit for Power Burn-in	20
6	Bias Conditions for Irradiation Testing	22
	NDICES (Applicable to specific Manufacturers only)	
'A'	Agreed Deviations for M/A-Com Ltd. (G.B.)	24



PAGE

5

ISSUE

1. **GENERAL**

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Diode, Microwave, Silicon, Tuning Varactor, based on Types ML4355 thru ML4365. It shall be read in conjunction with ESA/SCC Generic Specification No. 5010, the requirements of which are supplemented herein.

1.2 TYPE VARIANTS

Variants of the basic diodes specified herein, which are also covered by this specification are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the diodes specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 <u>FUNCTIONAL DIAGRAM</u>

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

1.7 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are Categorised as Class 2 with a Minimum Critical Path Failure Voltage of 3400V.

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.



PAGE 6

ISSUE 1

TABLE 1(a) - TYPE VARIANTS

VARIANT	(2) BASED ON TYPE	(3) FIGURE	TOTAL CAPACITANCE C _T (pF)		(5) QUALITY FACTOR (Q) (MINIMUM)	(6) BODY-LID AND LEAD MATERIAL AND FINISH
			MIN	MAX	,	
01	ML4355 - 30	2(a)	1.90	2.50	850	A7-D2
02	ML4355 - 31	2(b)	1.90	2.50	850	A7-D2
. 03	ML4355 - 36	2(c)	1.90	2.50	850	A7-D2
04	ML4355 - 103	2(d)	2.00	2.60	850	A7-D2
05	ML4355 - 118	2(e)	1.94	2.54	850	A7
06	ML4355 - 186	2(f)	1.85	2.45	850	D2
07	ML4356 - 30	2(a)	2.30	3.10	850	A7-D2
08	ML4356 - 31	2(b)	2.30	3.10	850	A7-D2
09	ML4356 - 36	2(c)	2.30	3.10	850	A7-D2
10	ML4356 - 103	2(d)	2.40	3.20	850	A7-D2
11	ML4356 - 118	2(e)	2.34	3.14	850	A7
12	ML4356 - 186	2(f)	2.25	3.05	850	D2
13	ML4357 - 30	2(a)	2.85	3.75	800	A7-D2
14	ML4357 - 31	2(b)	2.85	3.75	800	A7-D2
15	ML4357 - 36	2(c)	2.85	3.75	800	A7-D2
16	ML4357 - 103	2(d)	2.95	3.85	800	A7-D2
17	ML4357 - 118	2(e)	2.89	3.79	800	A7
18	ML4357 - 186	2(f)	2.80	3.70	800	D2
19	ML4358 - 30	2(a)	3.40	4.40	750	A7-D2
20	ML4358 - 31	2(b)	3.40	4.40	750	A7-D2
21	ML4358 - 36	2(c)	3.40	4.40	750	A7-D2
22	ML4358 - 103	2(d)	3.50	4.50	750	A7-D2
23	ML4358 - 118	2(e)	3.45	4.45	750	A7
24	ML4358 - 186	2(f)	3.35	4.35	750	D2
25	ML4359 - 30	2(a)	4.10	5.30	700	A7-D2
26	ML4359 - 31	2(b)	4.10	5.30	700	A7-D2
27	ML4359 - 36	2(c)	4.10	5.30	700	A7-D2
28	ML4359 - 103	2(d)	4.20	5.40	700	A7-D2
29	ML4359 - 118	2(e)	4.14	5.34	700	A7
30	ML4359 - 186	2(f)	4.05	5.25	700	D2
31	ML4360 - 30	2(a)	4.90	6.30	700	A7-D2
32	ML4360 - 31	2(b)	4.90	6.30	700	A7-D2
33	ML4360 - 36	2(c)	4.90	6.30	700	A7-D2
34	ML4360 - 103	2(d)	5.00	6.40	700	A7-D2
35	ML4360 - 118	2(e)	4.94	6.34	700	A7
36	ML4360 - 186	2(f)	4.85	6.25	700	D2



PAGE 7

ISSUE 1

TABLE 1(a) - TYPE VARIANTS (CONT'D)

VARIANT (1)	(2) BASED ON TYPE	(3) FIGURE	TOTAL CAPACITANCE C _T (pF)		(5) QUALITY FACTOR (Q) (MINIMUM)	(6) BODY-LID AND LEAD MATERIAL AND FINISH
			MIN	MAX	(Will Will Civi)	AND THAILT
37	ML4361 - 30	2(a)	5.90	7.70	600	A7-D2
38	ML4361 - 31	2(b)	5.90	7.70	600	A7-D2
39	ML4361 - 36	2(c)	5.90	7.70	600	A7-D2
40	ML4361 - 103	2(d)	6.00	7.80	600	A7-D2
41	ML4361 - 118	2(e)	5.94	7.74	600	A7
42	ML4361 - 186	2(f)	5.85	7.65	600	D2
43	ML4362 - 30	2(a)	7.20	9.20	600	A7-D2
44	ML4362 - 31	2(b)	7.20	9.20	600	A7-D2
45	ML4362 - 36	2(c)	7.20	9.20	600	A7-D2
46	ML4362 - 103	2(d)	7.30	9.30	600	A7-D2
47	ML4363 - 30	2(a)	8.70	11.30	500	A7-D2
48	ML4363 - 31	2(b)	8.70	11.30	500	A7-D2
49	ML4363 - 36	2(c)	8.70	11.30	500	A7-D2
50	ML4363 - 103	2(d)	8.80	11.40	500	A7-D2
51	ML4364 - 30	2(a)	10.60	13.40	500	A7-D2
52	ML4364 - 31	2(b)	10.60	13.40	500	A7-D2
53	ML4364 - 36	2(c)	10.60	13.40	500	A7-D2
54	ML4364 - 103	2(d)	10.70	13.50	500	A7-D2
55	ML4365 - 30	2(a)	13.00	17.00	500	A7-D2
56	ML4365 - 31	2(b)	13.00	17.00	500	A7-D2
57	ML4365 - 36	2(c)	13.00	17.00	500	A7-D2
58	ML4365 - 103	2(d)	13.10	17.10	500	A7-D2



PAGE 8

ISSUE 1

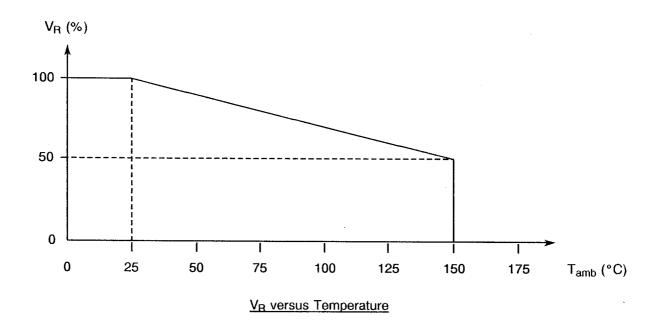
TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTIC	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	D.C. Reverse Voltage	V_{R}	-60	V	Note 1
2	Operating Temperature Range	T _{op}	-65 to +150	°C	T _{amb}
3	Storage Temperature Range	T _{stg}	-65 to +150	°C	
4	Soldering Temperature	T _{sol}	+ 230	°C	Note 2

NOTES

- 1. Measured at I_R = 10 μ A and T_{amb} = +25°C. For derating at T_{amb} > +25°C, see Figure 1.
- 2. Duration 5 seconds maximum (at a distance of not less than 1.5mm from the body for Variants 06, 12, 18, 24, 30, 36 and 42) and the same termination shall not be resoldered until 3 minutes have elapsed.

FIGURE 1 - PARAMETER DERATING INFORMATION





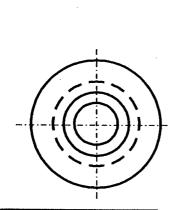
PAGE

ISSUE 1

9

FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - VARIANTS 01, 07, 13, 19, 25, 31, 37, 43, 47, 51, 55



	├ ── └ →	ЕВ		>
		->	B1 ←	
ØD1 Ød -	B2-	A		ØD
		— A		>
	(Cathode end		

SYMBOL	MILLIMETRES		
STWIBOL	MIN	MAX	
Α	5.20	5.72	
В	2.16	2.46	
B1	0.41	0.61	
B2	0.15	0.25	
Ød	1.52	1.63	
ØD	3.00	3.23	
ØD1	1.95	2.11	
L	1.52	1.63	

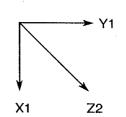
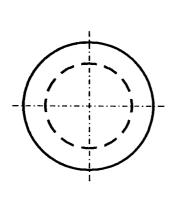
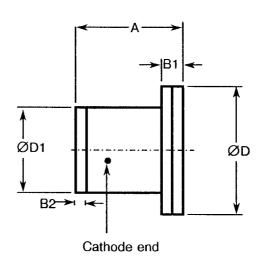
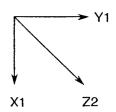


FIGURE 2(b) - VARIANTS 02, 08, 14, 20, 26, 32, 38, 44, 48, 52, 56



SYMBOL.	MILLIM	MILLIMETRES		
	MIN	MAX		
Α	2.16	2.46		
B1	0.41	0.61		
B2	0.15	0.25		
ØD	3.00	3.23		
ØD1 .	1.95	2.11		





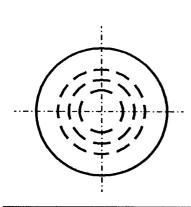


PAGE 10

ISSUE 1

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - VARIANTS 03, 09, 15, 21, 27, 33, 39, 45, 49, 53, 57



	A	
	<l→ <b< th=""><th></th></l→ <b<>	
	<u> </u>	
ØD1 Ød	B2→1 ← ØC)
	Cathode end	

SYMBOL	MILLIM	ETRES
STVIDOL	MIN	MAX
Α	3.60	4.18
В	2.16	2.46
B1	0.41	0.61
B2	0.15	0.25
Ød	1.52	1.63
ØD	3.00	3.23
ØD1	1.95	2.11
L	1.52	1.63

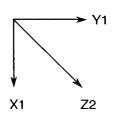
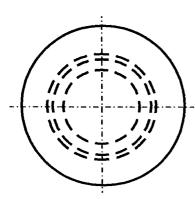
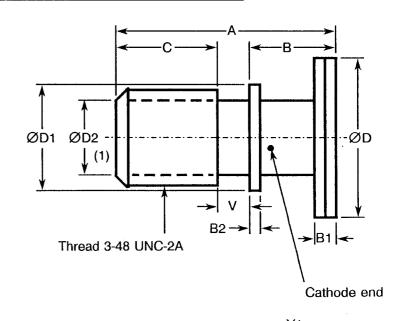
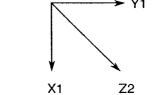


FIGURE 2(d) - VARIANTS 04, 10, 16, 22, 28, 34, 40, 46, 50, 54, 58



SYMBOL	MILLIMETRES		
STWIDOL	MIN	MAX	
Α	4.71	5.30	
В	1.47	1.80	
B1	0.41	0.61	
B2	0.20	0.30	
C	1.97	3.19	
ØD	3.00	3.23	
ØD1	2.49	2.59	
ØD2	1.60	2.00	
V	0.64	0.94	





NOTES
1. 6 spline socket, 1.39mm deep.

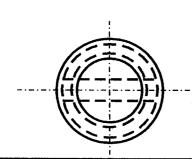


PAGE 11

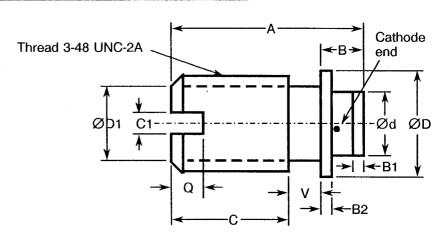
ISSUE 1

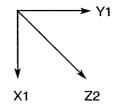
FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(e) - VARIANTS 05, 11, 17, 23, 29, 35, 41



SYMBOL	MILLIM	ETRES
STWIBOL	MIN	MAX
Α	4.19	4.70
В	0.77	1.04
B1	0.20	0.30
B2	0.22	0.28
С	2.21	3.29
C1	0.38	0.64
Ød	1.22	1.32
ØD	2.49	2.59
ØD1	1.60	2.00
Q	0.64	1.14
V	0.64	0.94





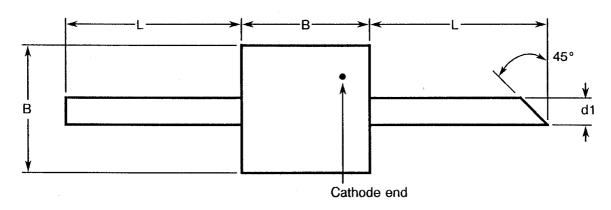


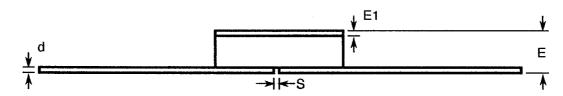
PAGE 12

ISSUE 1

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(f) - VARIANTS 06, 12, 18, 24, 30, 36, 42





SYMBOL	MILLIMETRES		
31WBOL	MIN	MAX	
В	2.39	2.62	
d	0.07	0.15	
d1	0.48	0.56	
E	0.79	1.12	
E1	0.10	0.18	
L	3.30	5.84	
S	0.10	-	

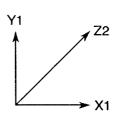


FIGURE 3 - FUNCTIONAL DIAGRAM



- 1. Anode
- 2. Cathode

NOTES

1. The cathode end shall be marked with a black dot or band. The marking will not be on the cathode connection but adjacent to it.



Rev. 'A'

PAGE 13

ISSUE 1

4. **REQUIREMENTS**

4.1 GENERAL

The complete requirements for procurement of the diodes specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 <u>DEVIATIONS FROM GENERIC SPECIFICATION</u>

4.2.1 <u>Deviations from Special In-process Controls</u>

- (a) Para. 5.2.3, Total Dose Irradiation Testing: Shall be performed during qualification and extension of qualification.
- (b) Para. 5.2.3, Total Dose Irradiation Testing: Shall be performed during procurement on a lot acceptance basis at the total dose irradiation level specified in the purchase order.
- (c) Quality Factor Measurement (Q): 3 randomly chosen samples shall be encapsulated in the type of package shown in Figure 2(a) of this specification. After encapsulation, Quality Factor measurements shall be performed using the method shown in Figure 4 of this specification with V_R = −4.0V. The limits specified in Table 1(a) of this specification shall be met.

4.2.2 <u>Deviations from Final Production Tests (Chart II)</u>

None.

4.2.3 <u>Deviations from Burn-in and Electrical Measurements (Chart III)</u>

(a) Para. 9.21, High Temperature Reverse Bias Burn-in: Shall be performed at 50% of rated V_R.

4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u>

(a) Para. 9.23, Special Testing: Shall not be performed.

4.2.5 <u>Deviations from Lot Acceptance Tests (Chart V)</u>

(a) Para. 9.23, Special Testing: Shall not be performed.

4.3 MECHANICAL AND ENVIRONMENTAL REQUIREMENTS

4.3.1 <u>Dimension Check</u>

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.



PAGE 14

ISSUE 1

4.3.2 Weight

The maximum weight of the diodes specified herein shall be:

Variant No.	Weight (g)
01, 07, 13, 19, 25, 31, 37, 43, 47, 51, 55	0.12
02, 08, 14, 20, 26, 32, 38, 44, 48, 52, 56	0.06
03, 09, 15, 21, 27, 33, 39, 45, 49, 53, 57	0.10

Variant No.	Weight (g)
04, 05, 10, 11, 16, 17, 22, 23, 28, 29, 34, 35, 40, 41, 46, 50, 54, 58	0.14
06, 12, 18, 24, 30, 36, 42	0.06

4.3.3 <u>Terminal Strength</u>

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5010. The test conditions shall be as follows:-

(a) Condition: 'A' (Tension)

Variants 06, 12, 18, 24, 30, 36 and 42:

Force: 5.1N.

Duration: 5 seconds.

(b) Condition: 'D2' (Stud Torque)

Variants 04, 10, 16, 22, 28, 34, 40. 46, 50, 54 and 58:

- Torque: 56mNm.

Duration: 5 seconds.

Variants 05, 11, 17, 23, 29, 35 and 41:

Torque: 42mNm.

Duration: 5 seconds.

(c) Condition: Compression

Variants 01, 02, 03, 04, 07, 08, 09, 10, 13, 14, 15, 16, 19, 20, 21, 22, 25, 26, 27, 28, 31, 32, 33, 34, 37, 38, 39, 40, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57 and 58:

Force: 50N.

- Duration: 5 seconds.

Variants 05, 11, 17, 23, 29, 35 and 41:

Force: 10N.

- Duration: 5 seconds.

The compression test shall be performed by applying the specified force to the end-cap by means of a suitable weight applied for the specified time. On completion of the test, a visual examination shall be performed to check for damage to the end-cap or the ceramic body.



PAGE 15

ISSUE 1

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material shall not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a ceramic body. The lid shall be brazed, welded or preform soldered.

4.4.2 Lead Materials and Finish

- (a) For Variants 01, 02, 03, 04, 07, 08, 09, 10, 13, 14, 15, 16, 19, 20, 21, 22, 25, 26, 27, 28, 31, 32, 33, 34, 37, 38, 39, 40, 43, 44, 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57 and 58, the body material shall be Type 'A' with Type '7' finish and the lid material shall be Type 'D' with Type '2' finish, in accordance with the requirements of ESA/SCC Basic Specification No. 23500.
- (b) For Variants 05, 11, 17, 23, 29, 35 and 41, the lead material shall be Type 'A' with Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.
- (c) For Variants 06, 12, 18, 24, 30, 36 and 42, the lead material shall be Type 'D' with Type '2' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.

4.5 MARKING

4.5.1 General

The marking of components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700 and the following paragraphs. When the component is too small to accommodate all of the marking specified, as much as space permits shall be marked and the marking information, in full, shall accompany the component in its primary package.

The information to be marked and the order of precedence, shall be as follows:-

- (a) Cathode Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Cathode Identification

Cathode identification shall be as shown in Figures 2 and 3 of this specification.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

EE1000701DE

	00120070101
Detail Specification Number —————	
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	
Total Dose Irradiation Level (if applicable)	

The Total Dose Irradiation Level designation shall be added for those devices for which a sample has been successfully tested to the level in question. For these devices, a code letter shall be added in accordance with the requirements of ESA/SCC Basic Specification No. 22900.



Rev. 'A'

PAGE 16

ISSUE 1

4.5.4 <u>Traceability Information</u>

Each component shall be marked in respect of traceability information as defined in ESA/SCC Basic Specification No. 21700.

4.6 <u>ELECTRICAL MEASUREMENTS</u>

4.6.1 <u>Electrical Measurements at Room Temperature</u>

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 <u>Electrical Measurements at High and Low Temperatures</u>

The parameters to be measured at high and low temperatures are scheduled in Table 3. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +150(+0-3)$ °C.

4.6.3 <u>Circuits for Electrical Measurements</u>

A circuit for use in performing the quality factor measurement is shown in Figure 4.

4.7 BURN-IN TESTS

Burn-in shall be Category 1 of Chart III(a).

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22±3 °C. The parameter drift values (Δ) applicable to the scheduled parameters shall not be exceeded. In addition to these drift value requirements for a given parameter, the appropriate limit value specified in Table 2 shall not be exceeded.

4.7.2 <u>Conditions for High Temperature Reverse Bias Burn-in</u>

The requirements for the high temperature reverse bias burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5010. The conditions for high temperature reverse bias burn-in shall be as specified in Table 5(a) of this specification.

4.7.3 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5010. The conditions for power burn-in shall be as specified in Table 5(b) of this specification.

4.7.4 <u>Electrical Circuits for High Temperature Reverse Bias and Power Burn-in</u>

Circuits for use in performing the H.T.R.B and power burn-in tests are shown in Figures 5(a) and 5(b) of this specification.



PAGE 17

ISSUE 1

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST CONDITIONS		MIL-STD-750 TEST CONDITIONS		IITS	UNIT
	OF WILL HOTEL HOTEL	OTWIDOL	TEST METHOD	LOT CONDITIONS	MIN.	MAX.	OINIT	
1	Reverse Current 1	I _{R1}	4016	V _R = -60V	-	10	μΑ	
2	Reverse Current 2	I _{R2}	4016	V _R = -30V	_	50	· nA	
3	Forward Voltage	V _F	4011	I _F = 100mA	-	1.0	٧	

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750	TEST	LIMITS		UNIT
140.	OTATAOTERIOTIOS	OTWIDOL	TEST METHOD CONDITIONS	CONDITIONS	MIN.	MAX.	ONIT
4	Total Capacitance	Ст	4001	V _R = -4.0V f = 1.0MHz	Not	e 1	pF
5	Total Capacitance Ratio	_	4001	$V_R = 0V$ $V_R = -60V$ $f = 1.0MHz$ Note 2 Variants 01 to 06 Variants 07 to 12 Variants 13 to 18 Variants 19 to 24 Variants 25 to 30 Variants 31 to 36 Variants 37 to 42 Variants 43 to 46 Variants 47 to 50 Variants 51 to 54 Variants 55 to 58	5.8 6.1 6.4 6.5 6.7 6.8 6.9 7.0 7.1 7.2 7.3	- - - - - - -	

NOTES

- 1. See Column 4 of Table 1(a).
- 2. Ratio = $\frac{C_T \text{ at } V_R = 0V}{C_T \text{ at } V_R = -60V}$



PAGE 18

ISSUE 1

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No.	CHARACTERISTICS	SVMROI	SPEC.AND/OR		LIM	ITS	UNIT
110.	OT A LA CALLAGA TO S	OTIVIDOL	TEST METHOD		MIN.	MAX.	CIVIT
2	Reverse Current 2	I _{R2}	As per Table 2	As per Table 2	-	10	μΑ

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC.AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2	Reverse Current 2	I _{R2}	As per Table 2	As per Table 2	± 10 (1) or (2) ± 100 (1)	nA %
3	Forward Voltage	V _F	As per Table 2	As per Table 2	± 100 (1)	mV

NOTES

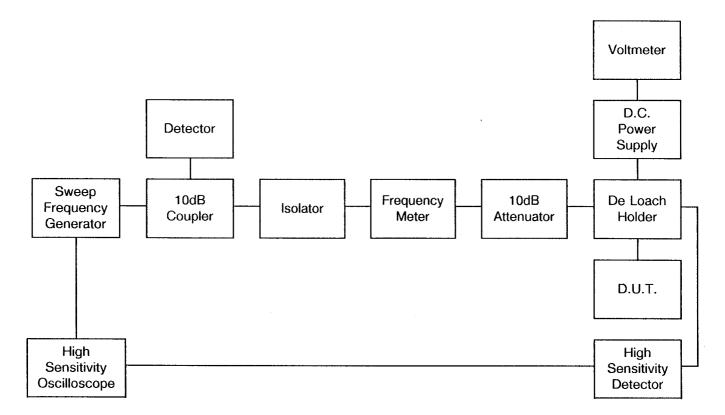
- 1. $\Delta 1 = \Delta 2$.
- 2. Whichever is the greater, referred to the initial measurement.



PAGE 19

ISSUE 1

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS





Rev. 'A'

PAGE 20

ISSUE 1

TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN AND OPERATING LIFE TESTS

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T _{amb}	+ 150(+ 0 - 3)	°C
2	Reverse Voltage	V _R	-30	V

TABLE 5(b) - CONDITIONS FOR POWER BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T _{amb}	+ 125(+ 0 - 3)	°C
2	Forward Current	l _F	25	mA

FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN AND OPERATING LIFE TESTS

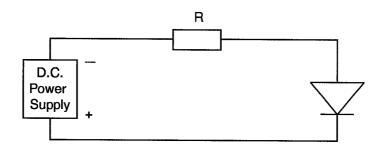
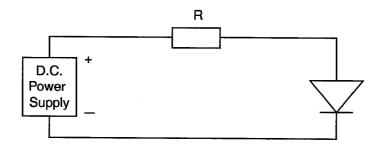


FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN





Rev. 'A'

PAGE 21

ISSUE 1

4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 5010)</u>

4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 <u>Electrical Measurements at Intermediate Points and on Completion of Endurance Tests</u>

The parameters to be measured at intermediate points and on completion of endurance tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5010. The conditions for operating life testing are specified in Table 5(a) of this specification.

4.8.4 <u>Electrical Circuits for Operating Life Tests</u>

The circuit to be used for performance of the operating life test shall be the same as shown in Figure 5(a) for High Temperature Reverse Bias Burn-in.

4.9 TOTAL DOSE IRRADIATION TESTING

4.9.1 Application

If specified in Para. 4.2.1 of this specification, total dose irradiation testing shall be performed in accordance with the requirements of ESA/SCC Basic Specification No. 22900.

4.9.2 Bias Conditions

Continuous bias shall be applied during irradiation testing as shown in Figure 6 of this specification.

4.9.3 <u>Electrical Measurements</u>

The parameters to be measured prior to irradiation exposure are scheduled in Table 2 of this specification. Only devices which meet the requirements of Table 2 shall be included in the test sample.

The parameters to be measured during and on completion of irradiation testing are scheduled in Table 7 of this specification.

4.10 SPECIAL TESTING

Not applicable.



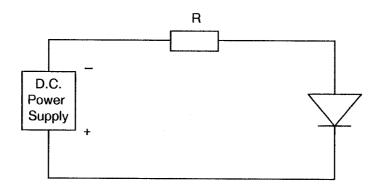
PAGE 22

ISSUE 1

TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS	UNIT
					MIN. MAX.	
1	Reverse Current 1	I _{R1}	As per Table 2	As per Table 2	As per Table 2	μΑ
2	Reverse Current 2	I _{R2}	As per Table 2	As per Table 2	As per Table 2	nA
3	Forward Voltage	V _F	As per Table 2	As per Table 2	As per Table 2	V
4	Total Capacitance	C _T	As per Table 2	As per Table 2	As per Table 2	ρF

FIGURE 6 - BIAS CONDITIONS FOR IRRADIATION TESTING



NOTES

1. A reverse bias of $V_R = -30V$, shall be applied.



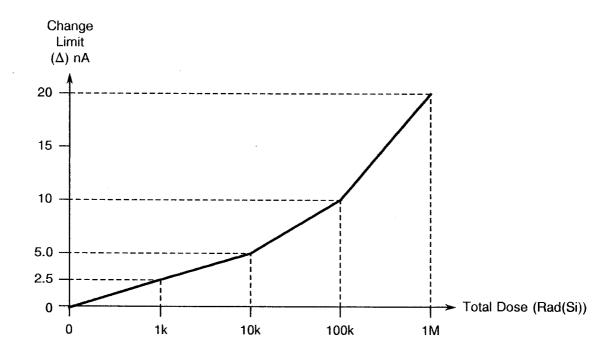
PAGE 23 ISSUE 1

TABLE 7 - ELECTRICAL MEASUREMENTS DURING AND ON COMPLETION OF IRRADIATION TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2	Reverse Current 2	l _{R2}	As per Table 2	As per Table 2	Note 1	n _. A

NOTES

1. The graph given below shall be used to determine the maximum permitted change.





PAGE 24

ISSUE 1

APPENDIX 'A'

Page 1 of 1

AGREED DEVIATIONS FOR M/A-Com LTD. (G.B.)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS	
Para. 4.2.2	Para. 9.4, "High Temperature Stabilisation Bake": May be performed at +150(+0-3) °C.	